

PHP45NQ10T

N-channel TrenchMOS standard level FET Rev. 02 — 8 July 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC convertors

Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V			
I_D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V$	-	-	47	Α			
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	150	W			
Static chara	acteristics								
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	22	25	mΩ			
Dynamic ch	Dynamic characteristics								
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 45 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C}$	-	25	-	nC			



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EA)
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PHP45NQ10T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}$	-	33	Α
		V _{GS} = 10 V; T _{mb} = 25 °C	-	47	Α
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	188	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T _{mb} = 25 °C	-	47	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	188	Α
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 40 A; V_{sup} ≤ 25 V; unclamped; t_p = 100 μs ; R_{GS} = 50 Ω	-	260	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; unclamped$	-	47	Α

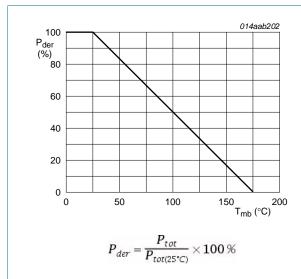


Fig 1. Normalized total power dissipation as a function of mounting base temperature

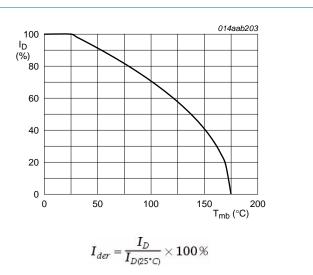


Fig 2. Normalized continuous drain current as a function of mounting base temperature

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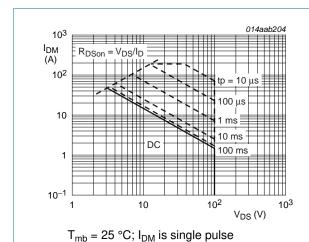


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

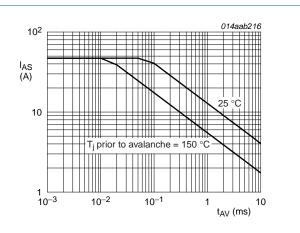


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

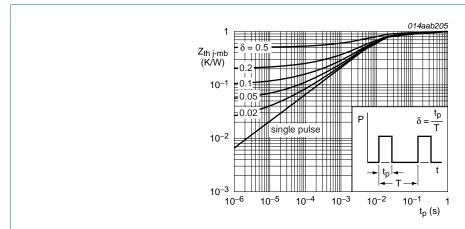


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = -55 \text{ °C}$	89	-	-	V
(,	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C}$	-	-	68	mΩ
resistance		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	22	25	mΩ
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	13	-	nC
Q_{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2600	-	pF
Coss	output capacitance	T _j = 25 °C	-	340	-	pF
C _{rss}	reverse transfer capacitance		-	195	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_L = 1.8 Ω ; V_{GS} = 10 V;	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	72	-	ns
$t_{d(off)}$	turn-off delay time		-	69	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain	from tab to centre of die ; $T_j = 25$ °C	-	3.5	-	nΗ
	inductance	from drain lead to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	4.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-di	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	82	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.26	-	μC

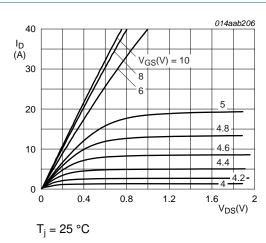


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

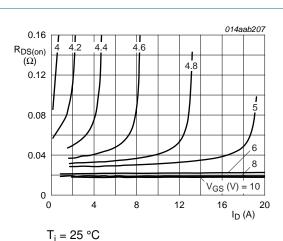


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

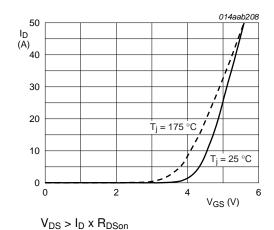


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

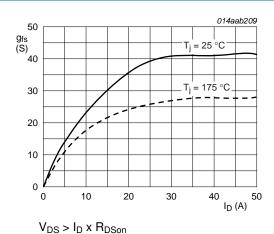


Fig 9. Forward transconductance as a function of drain current; typical values

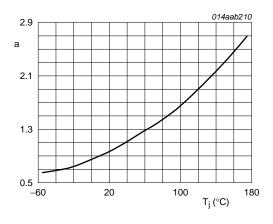


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

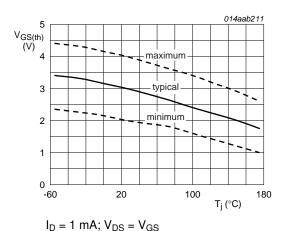


Fig 11. Gate-source threshold voltage as a function of junction temperature

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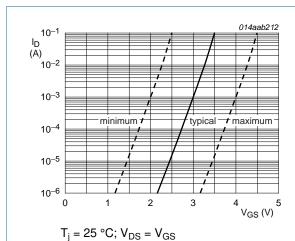
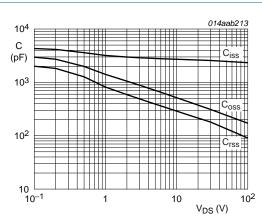
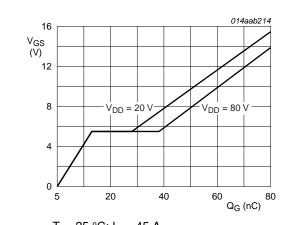


Fig 12. Sub-threshold drain current as a function of gate-source voltage



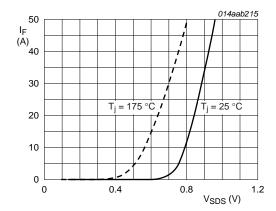
 $V_{GS} = 0 V$; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 T_j = 25 °C; I_D = 45 A Fig 14. Gate-source voltage as a function of gate

charge; typical values



 $V_{GS} = 0 V$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78 mounting D_1 base D L₁(1) $L_2^{(1)}$ Q $(3\times)$ b₂(2) (2×) 0 5 10 mm scale **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		$ \ \ \bigoplus \bigoplus$	08-04-23 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP45NQ10T v.2	20100708	Product data sheet	-	PHB_PHP_PHW45NQ10T v.1
Modifications:		at of this data sheet has be of NXP Semiconductors	•	o comply with the new identity
	 Legal text 	ts have been adapted to t	the new company	name where appropriate.
	 Type num 	ber PHP45NQ10T separ	ated from data sh	eet PHB_PHP_PHW45NQ10T v.1.
PHB_PHP_PHW45NQ10T v.1	19990801	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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